NSN 5961-01-414-9170

Diode Semiconductor Device - Page 1 of 1



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Inclosure Material:
Plastic
Joint Electronic Device Engineering Council/jedec/case Outline Designation:
To-236ab
Mounting Method:
Terminal
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
100.0 reverse voltage, instantaneous
Current Rating Per Characteristic:
200.00 milliamperes source cutoff current preset and 500.00 milliamperes forward current, average preset
Power Rating Per Characteristic:
225.0 milliwatts small-signal input power, common-collector preset
Terminal Type And Quantity:
3 bonding pad
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:
No
Fiig:
A110a0